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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	120MHz
Connectivity	CANbus, Ethernet, I ² C, IrDA, LINbus, Memory Card, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LCD, POR, PWM, WDT
Number of I/O	140
Program Memory Size	768KB (768K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	132K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	176-LQFP
Supplier Device Package	176-LQFP (24x24)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f207ift6

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**Table 3. STM32F207xx features and peripheral counts (continued)**

Peripherals		STM32F207Vx	STM32F207Zx	STM32F207Ix
Comm. interfaces	SPI/(I ² S)	3/(2) ⁽²⁾		
	I ² C	3		
	USART UART	4 2		
	USB OTG FS	Yes		
	USB OTG HS	Yes		
	CAN	2		
Camera interface		Yes		
GPIOs		82	114	140
SDIO		Yes		
12-bit ADC Number of channels		3		
		16	24	24
12-bit DAC Number of channels		Yes		
		2		
Maximum CPU frequency		120 MHz		
Operating voltage		1.8 V to 3.6 V ⁽³⁾		
Operating temperatures		Ambient temperatures: –40 to +85 °C/–40 to +105 °C		
		Junction temperature: –40 to + 125 °C		
Package		LQFP100	LQFP144	LQFP176/ UFBGA176

1. For the LQFP100 package, only FSMC Bank1 or Bank2 are available. Bank1 can only support a multiplexed NOR/PSRAM memory using the NE1 Chip Select. Bank2 can only support a 16- or 8-bit NAND Flash memory using the NCE2 Chip Select. The interrupt line cannot be used since Port G is not available in this package.
2. The SPI2 and SPI3 interfaces give the flexibility to work in an exclusive way in either the SPI mode or the I2S audio mode.
3. On devices in WLCSP64+2 package, if IRROFF is set to V_{DD}, the supply voltage can drop to 1.7 V when the device operates in the 0 to 70 °C temperature range using an external power supply supervisor (see [Section 3.16](#)).

1. The timers connected to APB2 are clocked from TIMxCLK up to 120 MHz, while the timers connected to APB1 are clocked from TIMxCLK up to 60 MHz.
2. The camera interface and Ethernet are available only in STM32F207xx devices.

Table 6. USART feature comparison

USART name	Standard features	Modem (RTS/CTS)	LIN	SPI master	IrDA	Smartcard (ISO 7816)	Max. baud rate in Mbit/s (oversampling by 16)	Max. baud rate in Mbit/s (oversampling by 8)	APB mapping
USART1	X	X	X	X	X	X	1.87	7.5	APB2 (max. 60 MHz)
USART2	X	X	X	X	X	X	1.87	3.75	APB1 (max. 30 MHz)
USART3	X	X	X	X	X	X	1.87	3.75	APB1 (max. 30 MHz)
UART4	X	-	X	-	X	-	1.87	3.75	APB1 (max. 30 MHz)
UART5	X	-	X	-	X	-	3.75	3.75	APB1 (max. 30 MHz)
USART6	X	X	X	X	X	X	3.75	7.5	APB2 (max. 60 MHz)

3.23 Serial peripheral interface (SPI)

The STM32F20x devices feature up to three SPIs in slave and master modes in full-duplex and simplex communication modes. SPI1 can communicate at up to 30 Mbits/s, while SPI2 and SPI3 can communicate at up to 15 Mbit/s. The 3-bit prescaler gives 8 master mode frequencies and the frame is configurable to 8 bits or 16 bits. The hardware CRC generation/verification supports basic SD Card/MMC modes. All SPIs can be served by the DMA controller.

The SPI interface can be configured to operate in TI mode for communications in master mode and slave mode.

3.24 Inter-integrated sound (I²S)

Two standard I²S interfaces (multiplexed with SPI2 and SPI3) are available. They can operate in master or slave mode, in half-duplex communication modes, and can be configured to operate with a 16-/32-bit resolution as input or output channels. Audio sampling frequencies from 8 kHz up to 192 kHz are supported. When either or both of the I²S interfaces is/are configured in master mode, the master clock can be output to the external DAC/CODEC at 256 times the sampling frequency.

All I2Sx interfaces can be served by the DMA controller.

3.25 SDIO

An SD/SDIO/MMC host interface is available, that supports MultiMediaCard System Specification Version 4.2 in three different databus modes: 1-bit (default), 4-bit and 8-bit.

3.37 Serial wire JTAG debug port (SWJ-DP)

The ARM SWJ-DP interface is embedded, and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target. The JTAG TMS and TCK pins are shared with SWDIO and SWCLK, respectively, and a specific sequence on the TMS pin is used to switch between JTAG-DP and SW-DP.

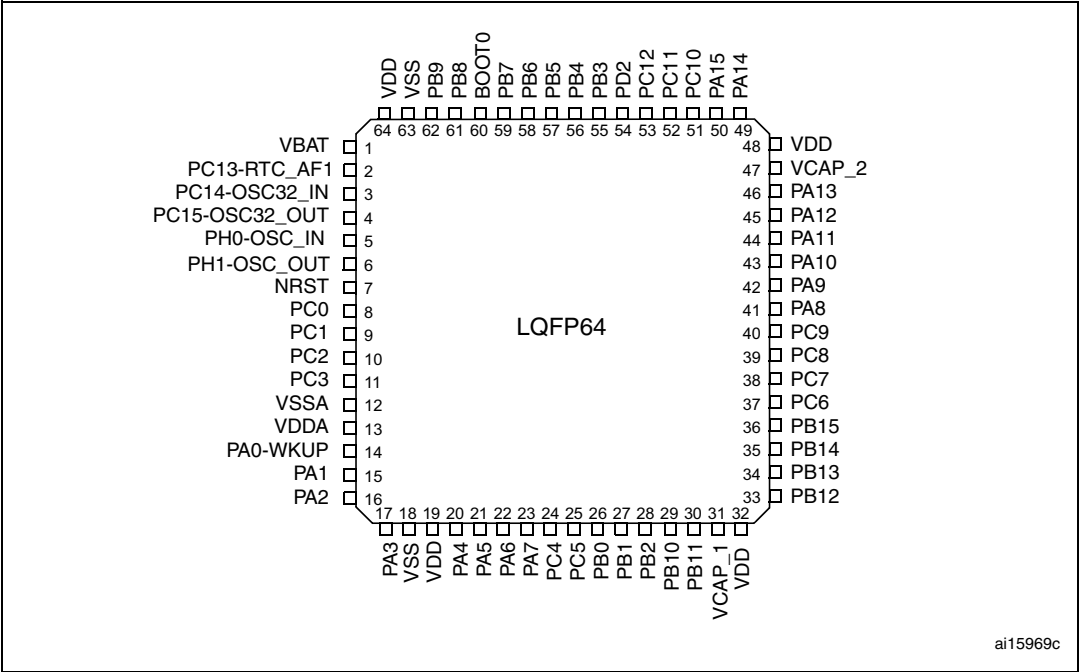
3.38 Embedded Trace Macrocell™

The ARM Embedded Trace Macrocell provides a greater visibility of the instruction and data flow inside the CPU core by streaming compressed data at a very high rate from the STM32F20x through a small number of ETM pins to an external hardware trace port analyzer (TPA) device. The TPA is connected to a host computer using USB, Ethernet, or any other high-speed channel. Real-time instruction and data flow activity can be recorded and then formatted for display on the host computer that runs the debugger software. TPA hardware is commercially available from common development tool vendors.

The Embedded Trace Macrocell operates with third party debugger software tools.

4 Pinouts and pin description

Figure 10. STM32F20x LQFP64 pinout



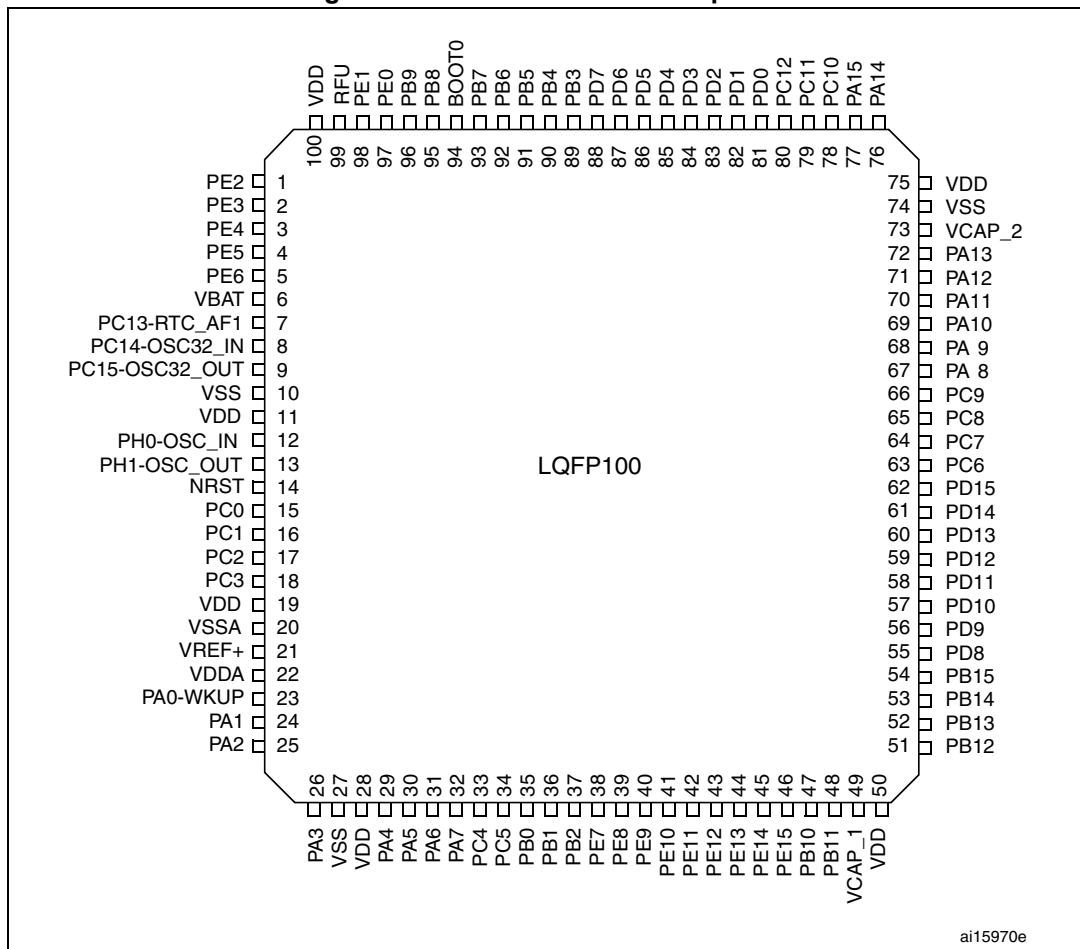
1. The above figure shows the package top view.

Figure 11. STM32F20x WLCSP64+2 ballout

	1	2	3	4	5	6	7	8	9
A	PA14	PA15	PC12	PB3	PB5	PB7	PB9	VDD	V _{BAT}
B	VSS	PA13	PC10	PB4	PB6	BOOT0	PB8	PC13	PC14
C	PA12	VCAP_2	PC11				PD2	IRROFF	PC15
D	PC9	PA11	PA10				PC2	VSS	VDD
E	VDD	PA8	PA9				PA0	NRST	PH0-OSC_IN
F	VSS	PC7	PC8				VREF+	PC1	PH1-OSC_OUT
G	PB15	PC6	PC5				PA3	PC3	PC0
H	PB14	PB13	PB10	PC4	PA6	PA5	REGOFF	PA1	VSS_5
J	PB12	PB11	VCAP_1	PB2	PB1	PB0	PA7	PA4	PA2

1. The above figure shows the package top view.

Figure 12. STM32F20x LQFP100 pinout



1. RFU means "reserved for future use". This pin can be tied to V_{DD} , V_{SS} or left unconnected.
2. The above figure shows the package top view.

Figure 15. STM32F20x UFBGA176 ballout

	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15																									
A	PE3	PE2	PE1	PE0	PB8	PB5	PG14	PG13	PB4	PB3	PD7	PC12	PA15	PA14	PA13																									
B	PE4	PE5	PE6	PB9	PB7	PB6	PG15	PG12	PG11	PG10	PD6	PD0	PC11	PC10	PA12																									
C	VBAT	PI7	PI6	PI5	VDD	RFU	VDD	VDD	VDD	PG9	PD5	PD1	PI3	PI2	PA11																									
D	PC13-TAMP1	PI8-TAMP2	PI9	PI4	VSS	BOOT0	VSS	VSS	VSS	PD4	PD3	PD2	PH15	PI1	PA10																									
E	PC14-OSC32_IN	PF0	PI10	PI11	<table><tr><td>VSS</td><td>VSS</td><td>VSS</td><td>VSS</td><td>VSS</td></tr><tr><td>VSS</td><td>VSS</td><td>VSS</td><td>VSS</td><td>VSS</td></tr><tr><td>VSS</td><td>VSS</td><td>VSS</td><td>VSS</td><td>VSS</td></tr><tr><td>VSS</td><td>VSS</td><td>VSS</td><td>VSS</td><td>VSS</td></tr><tr><td>VSS</td><td>VSS</td><td>VSS</td><td>VSS</td><td>VSS</td></tr></table>							VSS	VSS	VSS	VSS	VSS	VSS	VSS	VSS	VSS	VSS	VSS	VSS	VSS	VSS	VSS	VSS	VSS	VSS	VSS	VSS	VSS	VSS	VSS	VSS	VSS	PH13	PH14	PI0	PA9
VSS	VSS	VSS	VSS	VSS																																				
VSS	VSS	VSS	VSS	VSS																																				
VSS	VSS	VSS	VSS	VSS																																				
VSS	VSS	VSS	VSS	VSS																																				
VSS	VSS	VSS	VSS	VSS																																				
F	PC15-OSC32_OUT	VSS	VDD	PH2	VSS	VCAP_2	PC9	PA8																																
G	PH0-OSC_IN	VSS	VDD	PH3	VSS	VDD	PC8	PC7																																
H	PH1-OSC_OUT	PF2	PF1	PH4	VSS	VDD	PG8	PC6																																
J	NRST	PF3	PF4	PH5	VDD	VDD	PG7	PG6																																
K	PF7	PF6	PF5	VDD	PH12	PG5	PG4	PG3																																
L	PF10	PF9	PF8	REGOFF								PH11	PH10	PD15	PG2																									
M	VSSA	PC0	PC1	PC2	PC3	PB2	PG1	VSS	VSS	VCAP_1	PH6	PH8	PH9	PD14	PD13																									
N	VREF-	PA1	PA0-WKUP	PA4	PC4	PF13	PG0	VDD	VDD	VDD	PE13	PH7	PD12	PD11	PD10																									
P	VREF+	PA2	PA6	PA5	PC5	PF12	PF15	PE8	PE9	PE11	PE14	PB12	PB13	PD9	PD8																									
R	VDDA	PA3	PA7	PB1	PB0	PF11	PF14	PE7	PE10	PE12	PE15	PB10	PB11	PB14	PB15																									

ai17293c

ai17293c

1. RFU means “reserved for future use”. This pin can be tied to V_{DD} , V_{SS} or left unconnected.
2. The above figure shows the package top view.

Table 7. Legend/abbreviations used in the pinout table

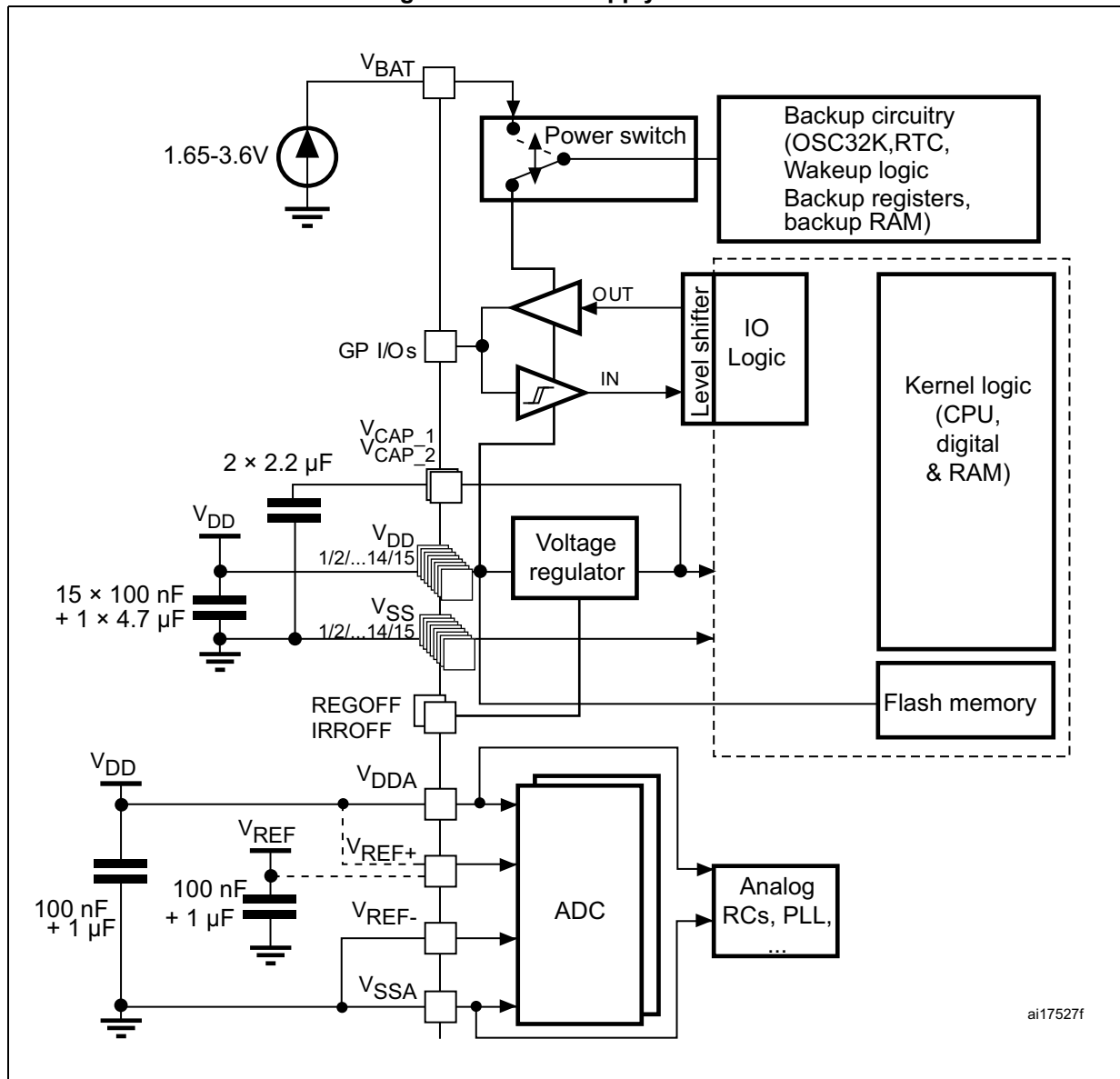
Name	Abbreviation	Definition
Pin name	Unless otherwise specified in brackets below the pin name, the pin function during and after reset is the same as the actual pin name	
Pin type	S	Supply pin
	I	Input only pin
	I/O	Input/ output pin
I/O structure	FT	5 V tolerant I/O
	TTa	3.3 V tolerant I/O
	B	Dedicated BOOT0 pin
	RST	Bidirectional reset pin with embedded weak pull-up resistor
Notes	Unless otherwise specified by a note, all I/Os are set as floating inputs during and after reset	
Alternate functions	Functions selected through GPIOx_AFR registers	
Additional functions	Functions directly selected/enabled through peripheral registers	

Table 8. STM32F20x pin and ball definitions (continued)

Pins						Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Note	Alternate functions	Additional functions
LQFP64	WLCSP64+2	LQFP100	LQFP144	LQFP176	UFBGA176						
-	-	-	131	159	C7	V _{DD}	S	-	-	-	-
-	-	-	132	160	B7	PG15	I/O	FT	-	USART6_CTS, DCM1_D13, EVENTOUT	-
55	A4	89	133	161	A10	PB3 (JTDO/TRACESWO)	I/O	FT	-	JTDO/ TRACESWO, SPI3_SCK, I2S3_SCK, TIM2_CH2, SPI1_SCK, EVENTOUT	-
56	B4	90	134	162	A9	PB4	I/O	FT	-	NJTRST, SPI3_MISO, TIM3_CH1, SPI1_MISO, EVENTOUT	-
57	A5	91	135	163	A6	PB5	I/O	FT	-	I2C1_SMBA, CAN2_RX, OTG_HS_ULPI_D7, ETH_PPS_OUT, TIM3_CH2, SPI1_MOSI, SPI3_MOSI, DCM1_D10, I2S3_SD, EVENTOUT	-
58	B5	92	136	164	B6	PB6	I/O	FT	-	I2C1_SCL,, TIM4_CH1, CAN2_TX, DCM1_D5, USART1_TX, EVENTOUT	-
59	A6	93	137	165	B5	PB7	I/O	FT	-	I2C1_SDA, FSMC_NL ⁽⁶⁾ , DCM1_VSYNC, USART1_RX, TIM4_CH2, EVENTOUT	-
60	B6	94	138	166	D6	BOOT0	I	B	-	-	V _{PP}
61	B7	95	139	167	A5	PB8	I/O	FT	-	TIM4_CH3, SDIO_D4, TIM10_CH1, DCM1_D6, ETH_MII_TXD3, I2C1_SCL, CAN1_RX, EVENTOUT	-
62	A7	96	140	168	B4	PB9	I/O	FT	-	SPI2_NSS, I2S2_WS, TIM4_CH4, TIM11_CH1, SDIO_D5, DCM1_D7, I2C1_SDA, CAN1_TX, EVENTOUT	-
-	-	97	141	169	A4	PE0	I/O	FT	-	TIM4_ETR, FSMC_NBL0, DCM1_D2, EVENTOUT	-

6.1.6 Power supply scheme

Figure 19. Power supply scheme



1. Each power supply pair must be decoupled with filtering ceramic capacitors as shown above. These capacitors must be placed as close as possible to, or below, the appropriate pins on the underside of the PCB to ensure the good functionality of the device.
2. To connect REGOFF and IRROFF pins, refer to [Section 3.16: Voltage regulator](#).
3. The two 2.2 μF ceramic capacitors should be replaced by two 100 nF decoupling capacitors when the voltage regulator is OFF.
4. The 4.7 μF ceramic capacitor must be connected to one of the V_{DD} pin.

Caution: Each power supply pair (V_{DD}/V_{SS} , V_{DDA}/V_{SSA} ...) must be decoupled with filtering ceramic capacitors as shown above. These capacitors must be placed as close as possible to, or below, the appropriate pins on the underside of the PCB, to ensure good device operation. It is not recommended to remove filtering capacitors to reduce PCB size or cost. This might cause incorrect device operation.

Table 15. Limitations depending on the operating power supply range

Operating power supply range	ADC operation	Maximum Flash memory access frequency (f_{Flashmax})	Number of wait states at maximum CPU frequency ($f_{\text{CPUmax}} = 120 \text{ MHz}$) ⁽¹⁾	I/O operation	FSMC_CLK frequency for synchronous accesses	Possible Flash memory operations
$V_{\text{DD}} = 1.8 \text{ to } 2.1 \text{ V}$ ⁽²⁾	Conversion time up to 1 Msps	16 MHz with no Flash memory wait state	7 ⁽³⁾	– Degraded speed performance – No I/O compensation	Up to 30 MHz	8-bit erase and program operations only
$V_{\text{DD}} = 2.1 \text{ to } 2.4 \text{ V}$	Conversion time up to 1 Msps	18 MHz with no Flash memory wait state	6 ⁽³⁾	– Degraded speed performance – No I/O compensation	Up to 30 MHz	16-bit erase and program operations
$V_{\text{DD}} = 2.4 \text{ to } 2.7 \text{ V}$	Conversion time up to 2 Msps	24 MHz with no Flash memory wait state	4 ⁽³⁾	– Degraded speed performance – I/O compensation works	Up to 48 MHz	16-bit erase and program operations
$V_{\text{DD}} = 2.7 \text{ to } 3.6 \text{ V}$ ⁽⁴⁾	Conversion time up to 2 Msps	30 MHz with no Flash memory wait state	3 ⁽³⁾	– Full-speed operation – I/O compensation works	– Up to 60 MHz when $V_{\text{DD}} = 3.0 \text{ to } 3.6 \text{ V}$ – Up to 48 MHz when $V_{\text{DD}} = 2.7 \text{ to } 3.0 \text{ V}$	32-bit erase and program operations

1. The number of wait states can be reduced by reducing the CPU frequency (see [Figure 21](#)).
2. On devices in WLCSP64+2 package, if IRROFF is set to V_{DD} , the supply voltage can drop to 1.7 V when the device operates in the 0 to 70 °C temperature range using an external power supply supervisor (see [Section 3.16](#)).
3. Thanks to the ART accelerator and the 128-bit Flash memory, the number of wait states given here does not impact the execution speed from Flash memory since the ART accelerator allows to achieve a performance equivalent to 0 wait state program execution.
4. The voltage range for OTG USB FS can drop down to 2.7 V. However it is degraded between 2.7 and 3 V.

6.3.3 Operating conditions at power-up / power-down (regulator ON)

Subject to general operating conditions for T_A .

Table 17. Operating conditions at power-up / power-down (regulator ON)

Symbol	Parameter	Min	Max	Unit
t_{VDD}	V_{DD} rise time rate	20	∞	$\mu\text{s/V}$
	V_{DD} fall time rate	20	∞	

6.3.4 Operating conditions at power-up / power-down (regulator OFF)

Subject to general operating conditions for T_A .

Table 18. Operating conditions at power-up / power-down (regulator OFF)

Symbol	Parameter	Conditions	Min	Max	Unit
t_{VDD}	V_{DD} rise time rate	Power-up	20	∞	$\mu\text{s/V}$
	V_{DD} fall time rate	Power-down	20	∞	
t_{VCAP}	V_{CAP_1} and V_{CAP_2} rise time rate	Power-up	20	∞	
	V_{CAP_1} and V_{CAP_2} fall time rate	Power-down	20	∞	

Table 19. Embedded reset and power control block characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{BOR2}	Brownout level 2 threshold	Falling edge	2.44	2.50	2.56	V
		Rising edge	2.53	2.59	2.63	V
V_{BOR3}	Brownout level 3 threshold	Falling edge	2.75	2.83	2.88	V
		Rising edge	2.85	2.92	2.97	V
$V_{BORhyst}^{(1)}$	BOR hysteresis	-	-	100	-	mV
$T_{RSTTEMPO}^{(1)(2)}$	Reset temporization	-	0.5	1.5	3.0	ms
$I_{RUSH}^{(1)}$	InRush current on voltage regulator power-on (POR or wakeup from Standby)	-	-	160	200	mA
$E_{RUSH}^{(1)}$	InRush energy on voltage regulator power-on (POR or wakeup from Standby)	$V_{DD} = 1.8\text{ V}$, $T_A = 105\text{ }^{\circ}\text{C}$, $I_{RUSH} = 171\text{ mA}$ for $31\text{ }\mu\text{s}$	-	-	5.4	μC

1. Guaranteed by design, not tested in production.

2. The reset temporization is measured from the power-on (POR reset or wakeup from V_{BAT}) to the instant when first instruction is read by the user application code.

6.3.6 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code.

The current consumption is measured as described in [Figure 20: Current consumption measurement scheme](#).

All Run mode current consumption measurements given in this section are performed using CoreMark code.

Table 21. Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator disabled)

Symbol	Parameter	Conditions	f _{HCLK}	Typ	Max ⁽¹⁾		Unit
				T _A = 25 °C	T _A = 85 °C	T _A = 105 °C	
I _{DD}	Supply current in Run mode	External clock ⁽²⁾ , all peripherals enabled ⁽³⁾	120 MHz	61	81	93	mA
			90 MHz	48	68	80	
			60 MHz	33	53	65	
			30 MHz	18	38	50	
			25 MHz	14	34	46	
			16 MHz ⁽⁴⁾	10	30	42	
			8 MHz	6	26	38	
			4 MHz	4	24	36	
			2 MHz	3	23	35	
		External clock ⁽²⁾ , all peripherals disabled	120 MHz	33	54	66	
			90 MHz	27	47	59	
			60 MHz	19	39	51	
			30 MHz	11	31	43	
			25 MHz	8	28	41	
			16 MHz ⁽⁴⁾	6	26	38	
			8 MHz	4	24	36	
			4 MHz	3	23	35	
			2 MHz	2	23	34	

1. Guaranteed by characterization results, tested in production at V_{DD} max and f_{HCLK} max with peripherals enabled.
2. External clock is 4 MHz and PLL is on when f_{HCLK} > 25 MHz.
3. When the ADC is on (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.6 mA per ADC for the analog part.
4. In this case HCLK = system clock/2.

Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78A IC latch-up standard.

Table 44. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	$T_A = +105\text{ }^{\circ}\text{C}$ conforming to JESD78A	II level A

6.3.15 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard, 3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (>5 LSB TUE), out of spec current injection on adjacent pins or other functional failure (for example reset, oscillator frequency deviation).

The test results are given in [Table 45](#).

Table 45. I/O current injection susceptibility⁽¹⁾

Symbol	Description	Functional susceptibility		Unit
		Negative injection	Positive injection	
I_{INJ}	Injected current on BOOT0 pin	−0	NA	mA
	Injected current on NRST pin	−0	NA	
	Injected current on TTa pins: PA4 and PA5	−0	+5	
	Injected current on all FT pins	−5	NA	

1. NA stands for “not applicable”.

Note: *It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.*

6.3.16 I/O port characteristics

General input/output characteristics

Unless otherwise specified, the parameters given in [Table 50](#) are derived from tests performed under the conditions summarized in [Table 14: General operating conditions](#).

All I/Os are CMOS and TTL compliant.

Table 46. I/O static characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{IL}	FT, TTa and NRST I/O input low level voltage	1.7 V≤V _{DD} ≤3.6 V	-	-	0.35V _{DD} −0.04 ⁽¹⁾	V
					0.3V _{DD} ⁽²⁾	
	BOOT0 I/O input low level voltage	1.75 V≤V _{DD} ≤3.6 V, −40 °C≤T _A ≤105 °C	-	-	0.1V _{DD} +0.1 ⁽¹⁾	
1.7 V≤V _{DD} ≤3.6 V, 0 °C≤T _A ≤105 °C		-	-			
V _{IH}	FT, TTa and NRST I/O input high level voltage ⁽⁵⁾	1.7 V≤V _{DD} ≤3.6 V	0.45V _{DD} +0.3 ⁽¹⁾	-	-	V
			0.7V _{DD} ⁽²⁾			
	BOOT0 I/O input high level voltage	1.75 V≤V _{DD} ≤3.6 V, −40 °C≤T _A ≤105 °C	0.17V _{DD} +0.7 ⁽¹⁾	-	-	
		1.7 V≤V _{DD} ≤3.6 V, 0 °C≤T _A ≤105 °C				
V _{HYS}	FT, TTa and NRST I/O input hysteresis	1.7 V≤V _{DD} ≤3.6 V	0.45V _{DD} +0.3 ⁽¹⁾	-	-	V
	BOOT0 I/O input hysteresis	1.75 V≤V _{DD} ≤3.6 V, −40 °C≤T _A ≤105 °C	10%V _{DDIO} ⁽¹⁾⁽³⁾	-	-	
			1.7 V≤V _{DD} ≤3.6 V, 0 °C≤T _A ≤105 °C	100 ⁽¹⁾	-	
I _{lkg}	I/O input leakage current ⁽⁴⁾	V _{SS} ≤V _{IN} ≤V _{DD}	-	-	±1	μA
	I/O FT input leakage current ⁽⁵⁾	V _{IN} = 5 V	-	-	3	

Table 46. I/O static characteristics (continued)

Symbol	Parameter		Conditions	Min	Typ	Max	Unit
R_{PU}	Weak pull-up equivalent resistor ⁽⁶⁾	All pins except for PA10/PB12 (OTG_FS_ID, OTG_HS_ID)	$V_{IN} = V_{SS}$	30	40	50	k Ω
		PA10/PB12 (OTG_FS_ID, OTG_HS_ID)	-	7	10	14	
R_{PD}	Weak pull-down equivalent resistor ⁽⁷⁾	All pins except for PA10/PB12 (OTG_FS_ID, OTG_HS_ID)	$V_{IN} = V_{DD}$	30	40	50	
		PA10/PB12 (OTG_FS_ID, OTG_HS_ID)	-	7	10	14	
C_{IO} ⁽⁸⁾	I/O pin capacitance		-	-	5	-	pF

1. Guaranteed by design, not tested in production.
2. Guaranteed by tests in production.
3. With a minimum of 200 mV.
4. Leakage could be higher than the maximum value, if negative current is injected on adjacent pins, Refer to [Table 45: I/O current injection susceptibility](#)
5. To sustain a voltage higher than VDD +0.3 V, the internal pull-up/pull-down resistors must be disabled. Leakage could be higher than the maximum value, if negative current is injected on adjacent pins. Refer to [Table 45: I/O current injection susceptibility](#)
6. Pull-up resistors are designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is minimum (~10% order).
7. Pull-down resistors are designed with a true resistance in series with a switchable NMOS. This NMOS contribution to the series resistance is minimum (~10% order).
8. Hysteresis voltage between Schmitt trigger switching levels. Based on characterization, not tested in production.

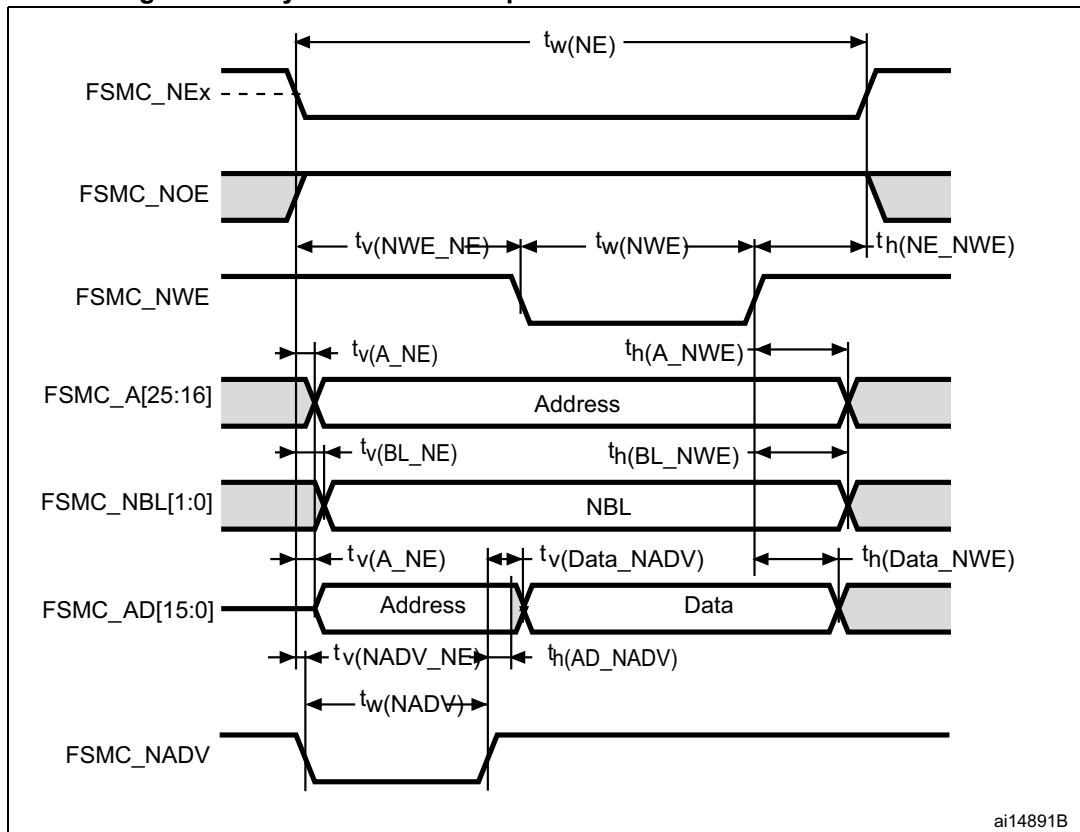
All I/Os are CMOS and TTL compliant (no software configuration required). Their characteristics cover more than the strict CMOS-technology or TTL parameters. The coverage of these requirements for FT I/Os is shown in [Figure 38](#).

Table 74. Asynchronous multiplexed PSRAM/NOR read timings⁽¹⁾⁽²⁾ (continued)

Symbol	Parameter	Min	Max	Unit
$t_{h(Data_NE)}$	Data hold time after FSMC_NEx high	0	-	ns
$t_{h(Data_NOE)}$	Data hold time after FSMC_NOE high	0	-	ns

1. $C_L = 30$ pF.

2. Guaranteed by characterization results, not tested in production.

Figure 60. Asynchronous multiplexed PSRAM/NOR write waveforms

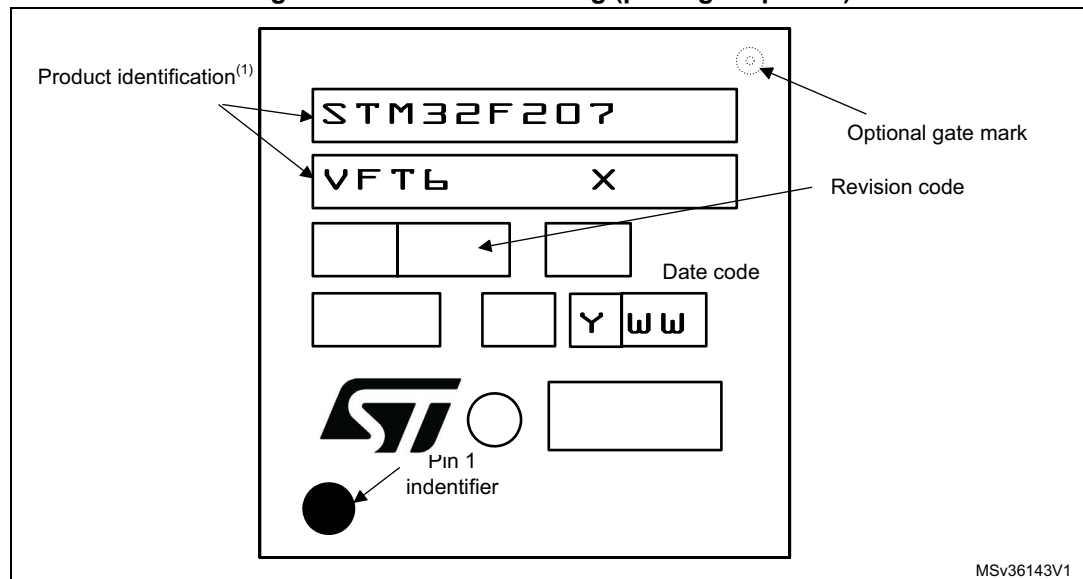
ai14891B

Table 75. Asynchronous multiplexed PSRAM/NOR write timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FSMC_NE low time	$4T_{HCLK}-1$	$4T_{HCLK}+1$	ns
$t_{v(NWE_NE)}$	FSMC_NEx low to FSMC_NWE low	$T_{HCLK}-1$	T_{HCLK}	ns
$t_{w(NWE)}$	FSMC_NWE low time	$2T_{HCLK}$	$2T_{HCLK}+1$	ns
$t_{h(NE_NWE)}$	FSMC_NWE high to FSMC_NE high hold time	$T_{HCLK}-1$	-	ns
$t_{v(A_NE)}$	FSMC_NEx low to FSMC_A valid	-	0	ns
$t_{v(NADV_NE)}$	FSMC_NEx low to FSMC_NADV low	1	2	ns
$t_{w(NADV)}$	FSMC_NADV low time	$T_{HCLK}-2$	$T_{HCLK}+2$	ns
$t_{h(AD_NADV)}$	FSMC_AD(address) valid hold time after FSMC_NADV high	T_{HCLK}	-	ns

Device marking

Figure 83. LQFP100 marking (package top view)



1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.